

AMENDMENTS TO THE CLAIMS

1-22. (Cancelled)

23. (Previously Presented) A method of forming a conductive pattern, comprising:
illuminating a photographic film with a desired illumination configuration;
developing the photographic film so that illuminated or non-illuminated portions of the film are adjusted to be in an altered state; and
selectively depositing additional conductive material onto portions of the film in an altered state in amounts greater than amounts of conductive material deposited on portions of the film not in the altered state,
wherein the additional conductive material is deposited via electroless deposition.

24. (Cancelled)

25. (Previously Presented) The method of claim 23 further comprising electroplating a metal on the conductive material deposited via the electroless deposition.

26. (Previously Presented) The method of claim 23 wherein the conductive pattern is a circuit.

27. (Previously Presented) A method of forming a discontinuous metallic structure comprising:
illuminating a photographic film with a desired structure configuration;
developing the photographic film so that illuminated or non-illuminated portions of the film are adjusted to be in an altered state; and
selectively depositing additional conductive material onto portions of the film in an altered state in amounts greater than amounts of conductive material deposited on portions of the film not in the altered state,
wherein the additional conductive material is deposited via electroless deposition.

28. (Cancelled)
29. (Previously Presented) The method of claim 27 wherein the additional conductive material is nickel.
30. (Previously Presented) The method of claim 23, wherein the additional conductive material is a metal.
31. (Previously Presented) The method of claim 25 wherein the metal is nickel.
32. (Previously Presented) The method of claim 23, wherein the photographic film comprises a metal atom precursor capable of conversion into elemental metal.
33. (Previously Presented) The method of claim 32, wherein the metal atom precursor is a metal salt.
34. (Previously Presented) The method of claim 33, wherein the metal salt is a silver halide.
35. (Previously Presented) The method of claim 23 wherein a planar dimension of a portion of the conductive pattern is less than about 100 μm in width.
36. (Previously Presented) The method of claim 23 wherein a planar dimension of a portion of the conductive pattern is less than about 50 μm in width.
37. (Previously Presented) The method of claim 23 wherein a planar dimension of a portion of the conductive pattern is about 30 μm in width.

38. (Previously Presented) The method of claim 23, wherein the additional conductive material is deposited proximate a first portion of the film in the altered state while essentially no conductive material is deposited proximate a second portion of the film not in the altered state.

39. (Currently Amended) The method of claim 23 further comprising using the conductive pattern to form a structure having ~~wherein at least a portion of the conductive pattern~~ has an aspect ratio of greater than or equal to about 5.

40. (Previously Presented) The method of claim 25, further comprising freeing the metal from the article.

41. (Previously Presented) The method of claim 27 further comprising electroplating a metal on the conductive material deposited via the electroless deposition.

42. (Previously Presented) The method of claim 27, wherein the photographic film comprises a metal atom precursor capable of conversion into elemental metal.

43. (Previously Presented) The method of claim 42, wherein the metal atom precursor is a metal salt.

44. (Previously Presented) The method of claim 43, wherein the metal salt is a silver halide.

45. (Currently Amended) The method of claim 27 wherein a planar dimension of a portion of ~~the conductive pattern~~ discontinuous metallic structure is less than about 100 μm in width.

46. (Currently Amended) The method of claim 27 wherein a planar dimension of a portion of ~~the conductive pattern~~ discontinuous metallic structure is less than about 50 μm in width.

47. (Currently Amended) The method of claim 27 wherein a planar dimension of a portion of ~~the conductive pattern~~ discontinuous metallic structure is about 30 μm in width.

48. (Previously Presented) The method of claim 27, wherein the additional conductive material is deposited proximate a first portion of the film in the altered state while essentially no conductive material is deposited proximate a second portion of the film not in the altered state.

49. (Currently Amended) The method of claim 27 wherein at least a portion of the ~~conductive pattern~~ discontinuous metallic structure has an aspect ratio of greater than or equal to about 5.

50. (Previously Presented) The method of claim 41, further comprising freeing the metal from the article.